

## Furnaces 2"

- **All tubes can handle 2 inch wafers**
- **Pyrogenic oxidation furnace** - Temperature up to 1150 C – gases H<sub>2</sub> and O<sub>2</sub>
- **Double walled furnaces:** Uniform growth of oxide – only dry oxidation of silicon wafers
- **Compound semiconductor furnace:** This furnace is used for various compound semiconductor (GaN, GaAs etc) processes
- **Post Metallization Anneal (PMA) furnace:** This furnace is dedicated to post aluminum annealing
- **Annealing Furnace (Argon Ambient):** Max. Temp. : 900oC, Ambient : Argon
- **Boron Diffusion furnace:** Dedicated for making junctions in Si with solid source dopant and spin on dopant. Max. temp. is 1100oC, gases used: O<sub>2</sub>, H<sub>2</sub> & N<sub>2</sub>
- **Phosphorus Diffusion furnace:** Dedicated for making junctions in Si with solid source dopant and spin on dopant. Max. temp. is 1100 oC, gases used: O<sub>2</sub>, H<sub>2</sub> & N<sub>2</sub>

